

Product Summary

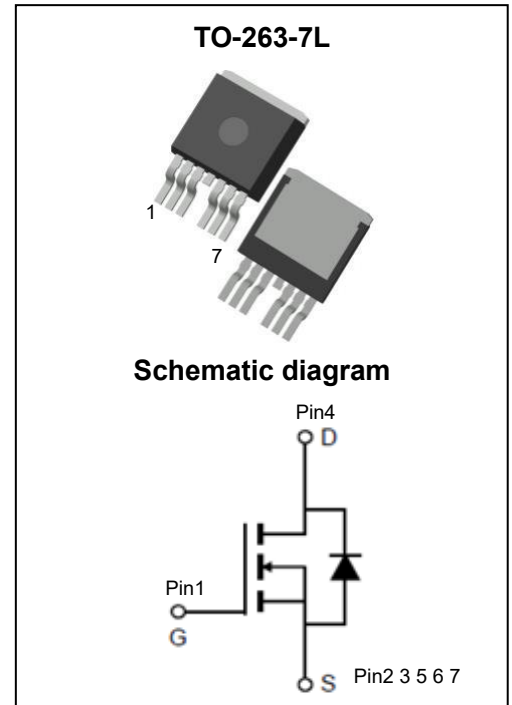
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	1.78mΩ@10V	320A

Feature

- Excellent Gate Charge x $R_{DS(on)}$ Product(FOM)
- Split Gate Trench Technology
- Extremely Low On-Resistance $R_{DS(on)}$

Application

- DC/DC Converter
- Power Management Switches
- BLDC Motor drive systems
- Battery Management



Package Marking and Ordering Information

Part Number	Package	Marking	Packing	Reel Size	Tape Width	Qty
GPT018N10NTQ	TO-263-7L	T018N10N	Reel&Tape	N/A	N/A	800pcs

ABSOLUTE MAXIMUM RATINGS ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	100	V
Gate - Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	$T_C = 25^{\circ}C$	320
		$T_C = 100^{\circ}C$	208
Pulsed Drain Current	I_{DM}	1176	A
Single Pulsed Avalanche Energy	E_{AS}	1936	mJ
Power Dissipation	P_D	250	W
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	42	$^{\circ}C/W$
Thermal Resistance From Junction To Case	$R_{\theta JC}$	0.5	$^{\circ}C/W$
Operating Junction And Storage Temperature	T_J, T_{STG}	-55~ +150	$^{\circ}C$

MOSFET ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100V, V _{GS} = 0V T _J = 25°C			1	μA
Gate - Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2	2.9	4	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 100A		1.78	2	mΩ
Forward Transconductance	g _{fs}	V _{DS} = 5V, I _D = 100A		238		S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = 50V, V _{GS} = 0V, f = 1MHz		10120		pF
Output Capacitance	C _{oss}			1360		
Reverse Transfer Capacitance	C _{rss}			50		
Gate Resistance	R _G	f=1MHz		1.2		Ω
Switching Characteristics⁵						
Total Gate Charge	Q _g	V _{DS} = 50V, V _{GS} = 10V, I _D = 50A		175		nC
Gate-Source Charge	Q _{gs}			48		
Gate-Drain Charge	Q _{gd}			53		
Turn-On Delay Time	t _{d(on)}	V _{DS} = 50V, V _{GS} = 10V, R _L = 6Ω		85		ns
Turn-On Rise Time	t _r			138		
Turn-Off Delay Time	t _{d(off)}			93		
Turn-Off Fall Time	t _f			98		
Source - Drain Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} = 0V, I _S = 100A		0.8	1.2	V
Reverse Recovery Time	t _{rr}	I _F = 50A, di/dt = 100A/us		80		ns
Reverse Recovery Charge	Q _{rr}				180	

Typical Characteristics

Fig.1 Typ. transfer characteristics

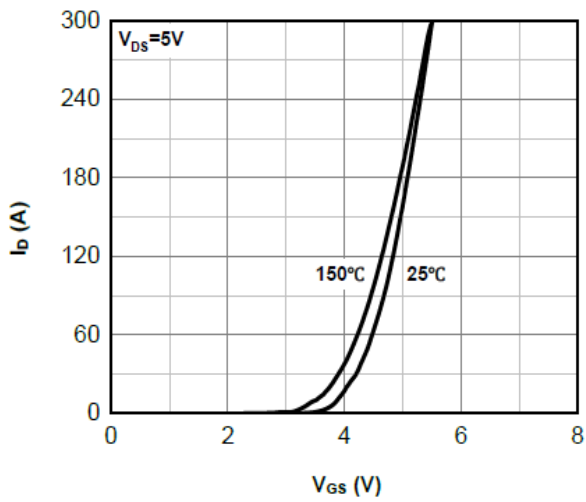


Fig.2 Typ. output characteristics

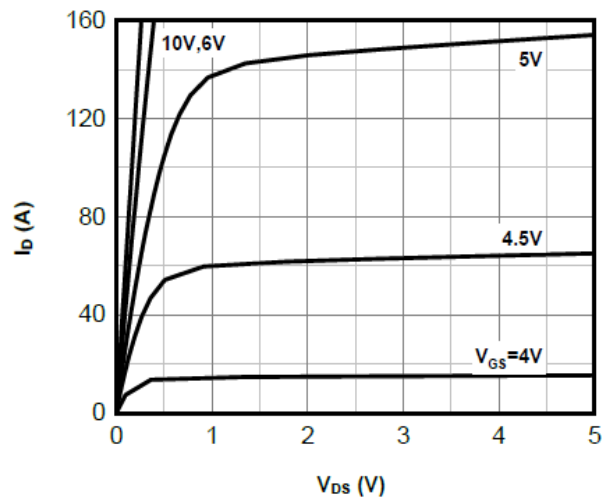


Fig.3 Normalized on-resistance vs drain current

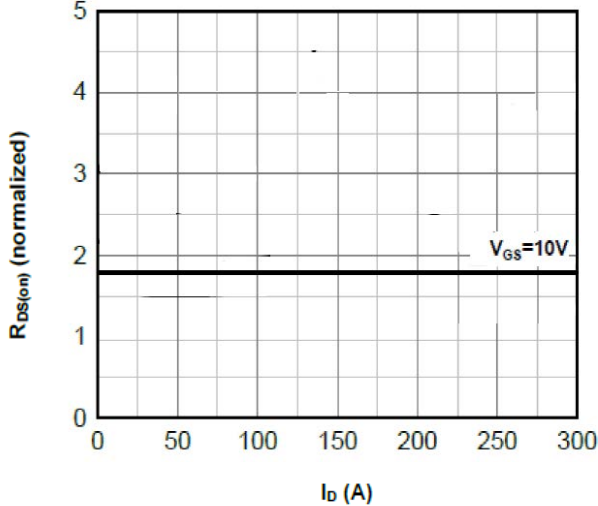


Fig.4 Typ. on-resistance vs gate-source voltage

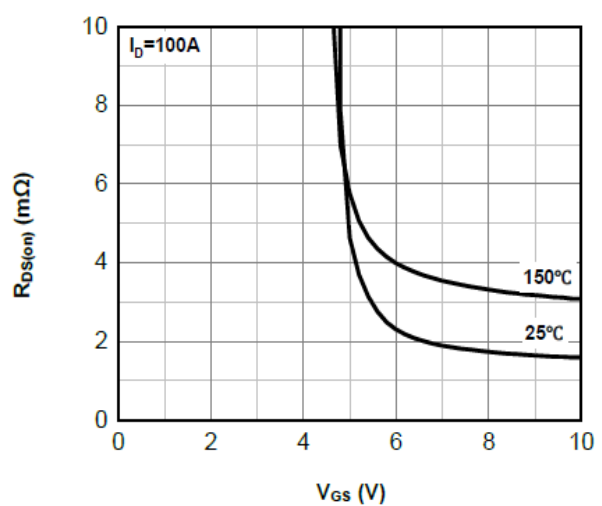


Fig.5 Normalized on-resistance vs junction temperature

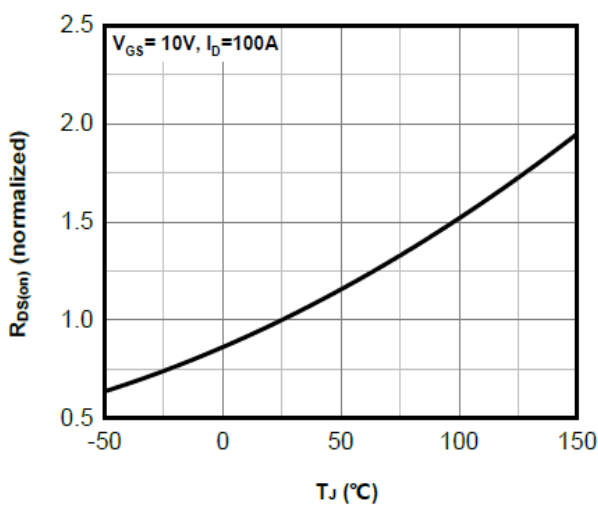
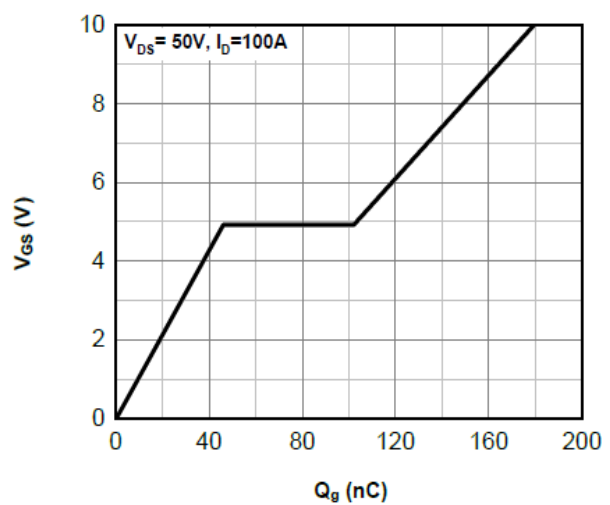


Fig.6 Typ. gate charge



Typical Characteristics

Fig.7 Typ. forward characteristics of body diode

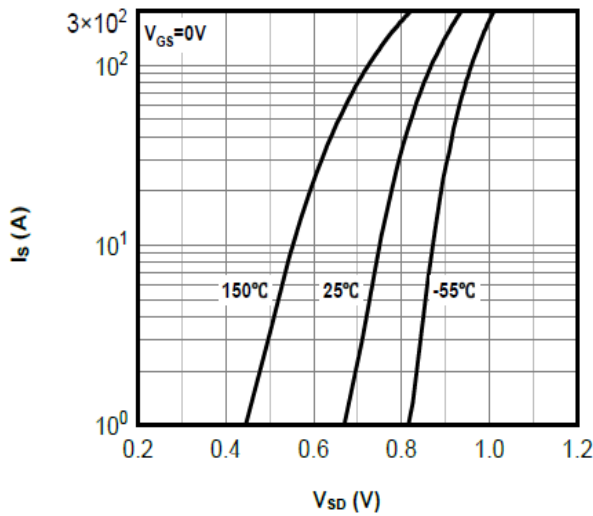


Fig.8 Safe operating area

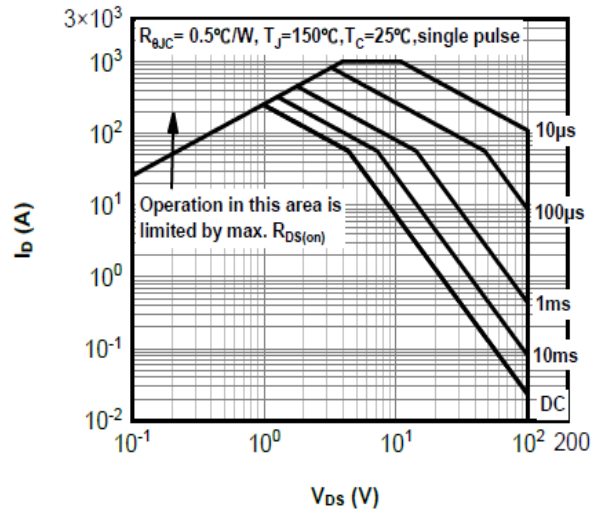


Fig.9 Typ. Capacitance

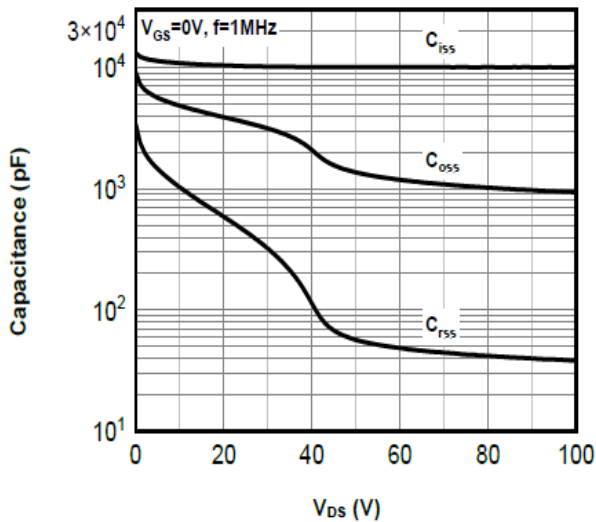


Fig.10 Single pulse maximum power dissipation

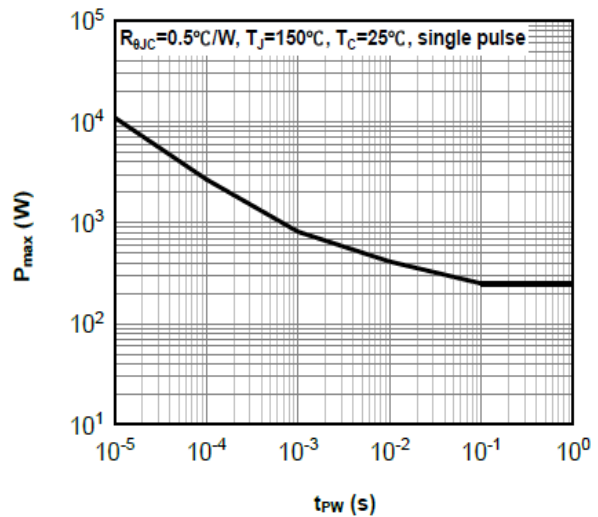


Fig.11 Max. power dissipation vs case temperature

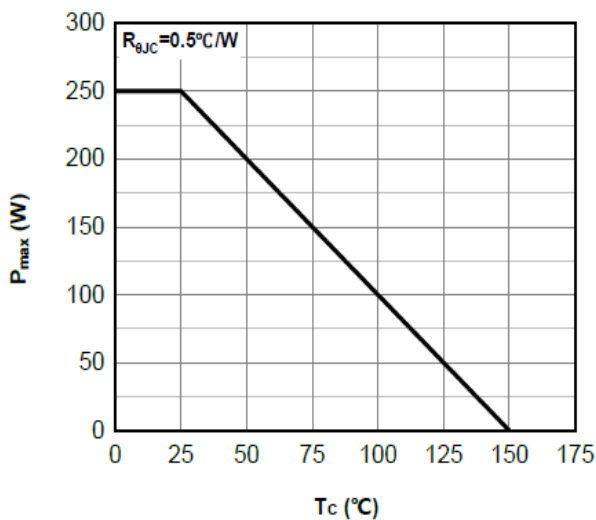
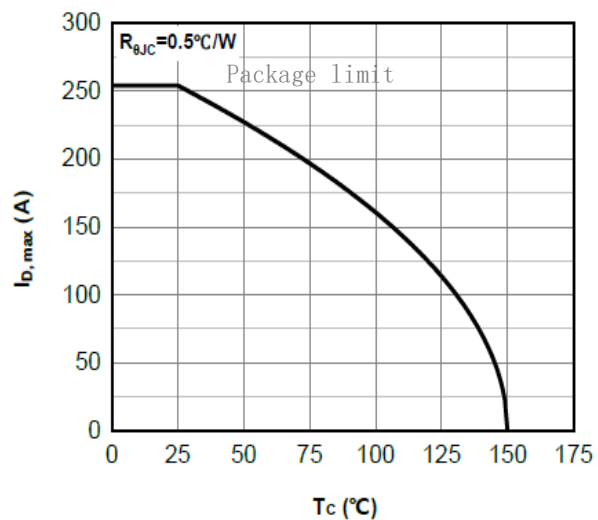


Fig.12 Max. continuous drain current vs case temperature



Typical Characteristics

Fig.13 Normalized $V_{(BR)DSS}$ vs junction temperature

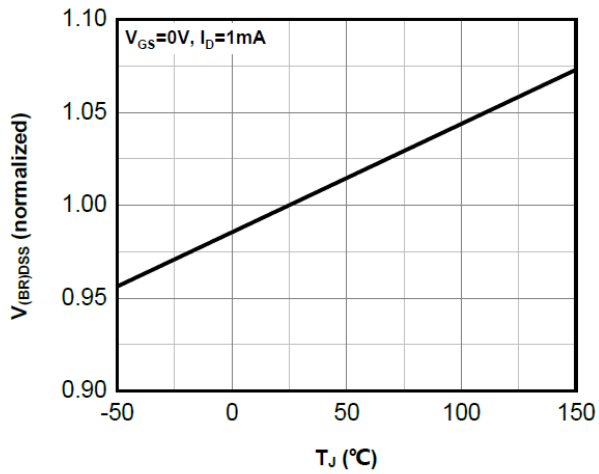


Fig.14 Normalized $V_{GS(th)}$ vs junction temperature

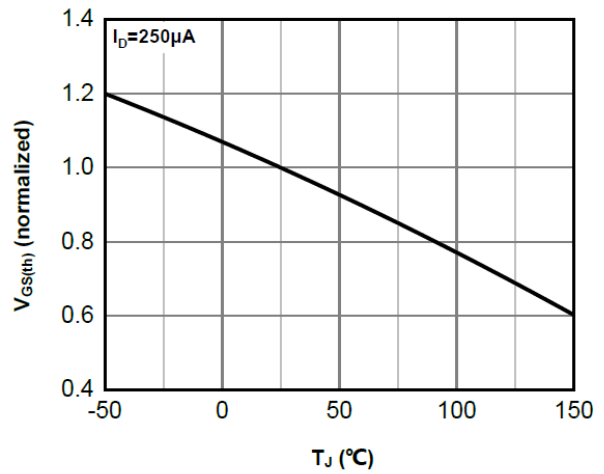
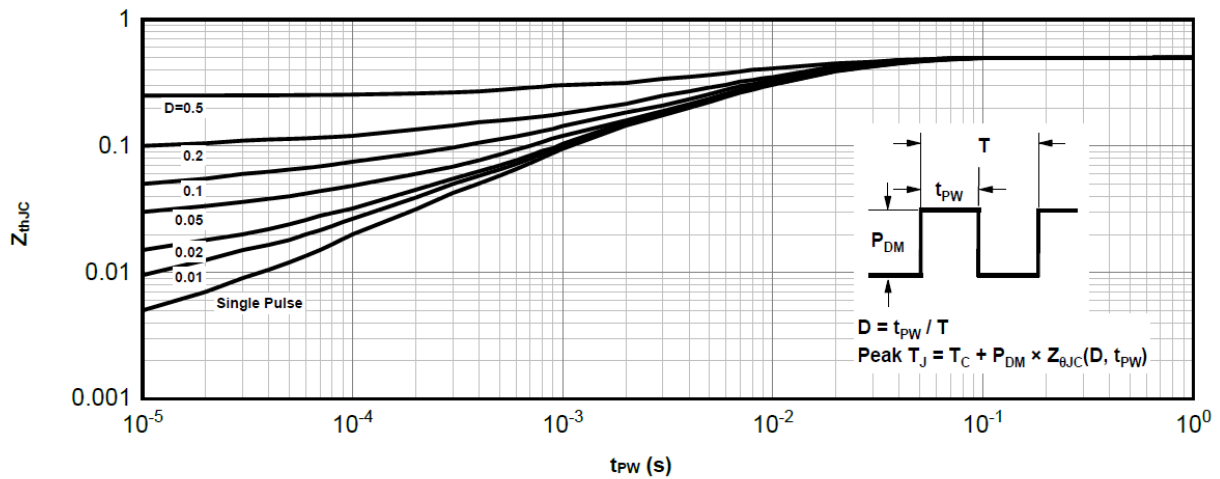
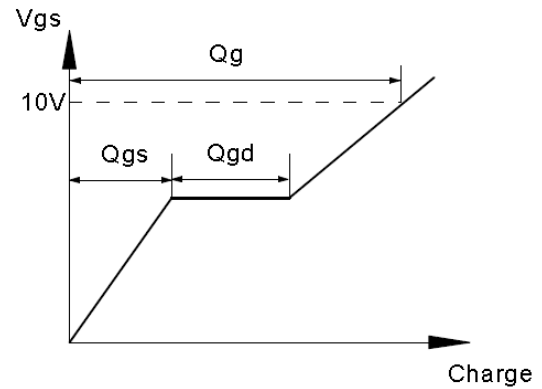
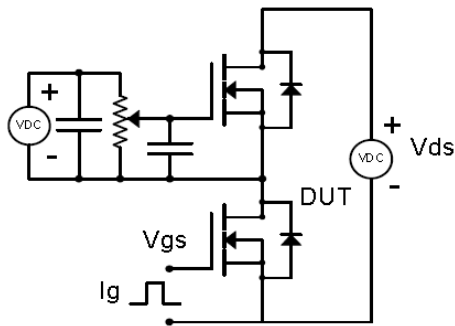


Fig.15 Transient thermal impedance from junction to case

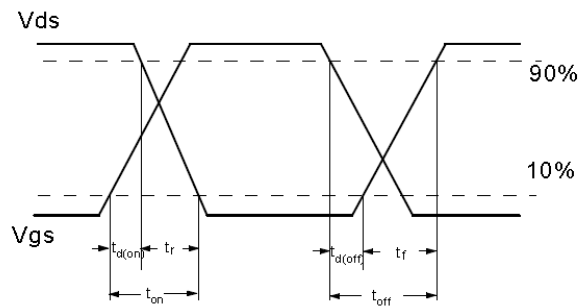
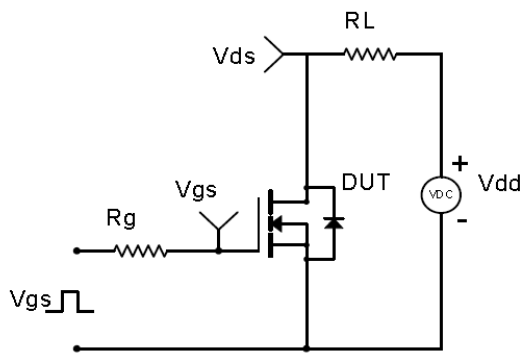


Test Circuit

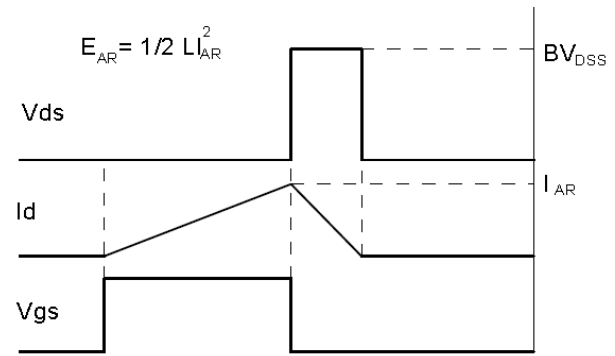
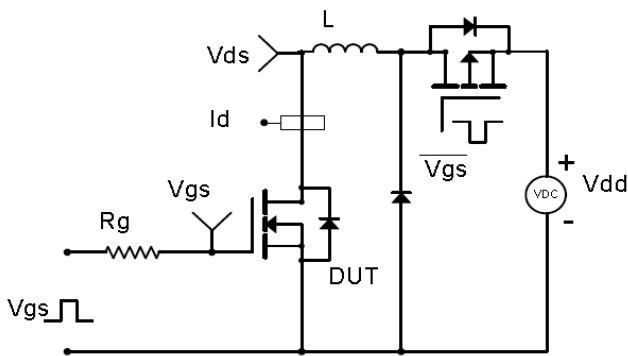
Gate Charge Test Circuit & Waveform



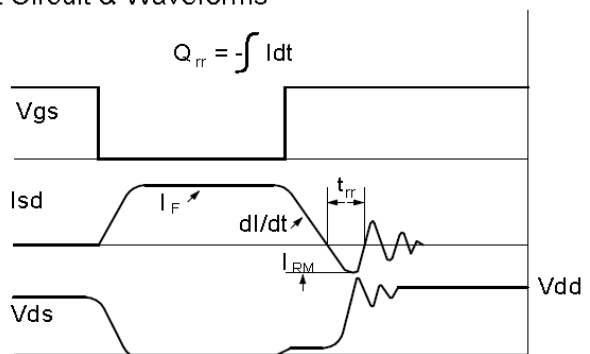
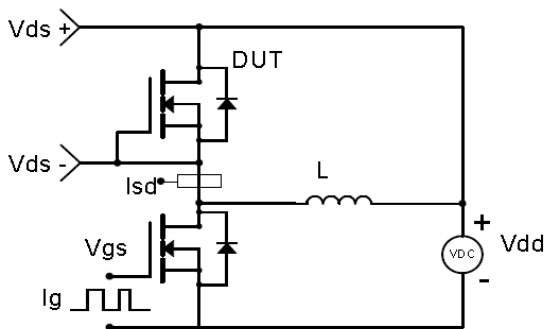
Resistive Switching Test Circuit & Waveforms

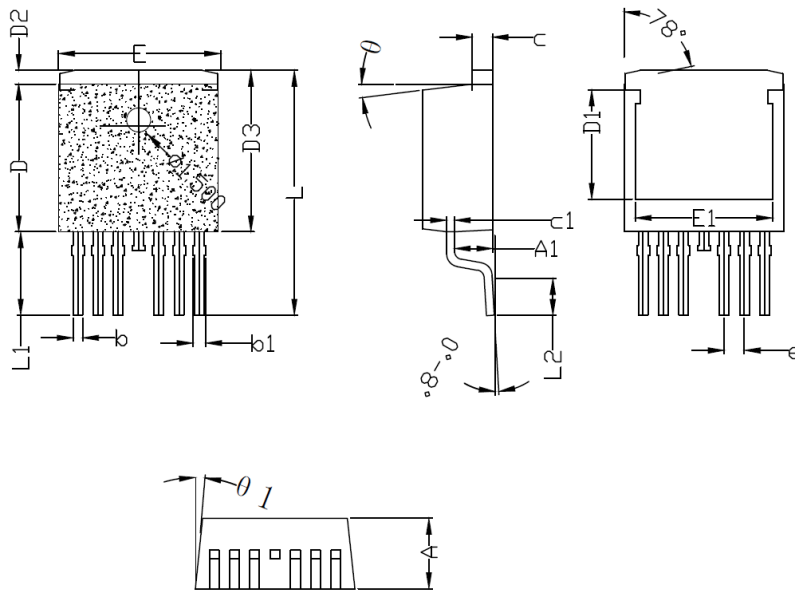


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



TO-263-7L Package Information


Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min.	Max.		Min.	Max.
A	4.2	4.6	D3	9.9	10.3
A1	2.3	2.5	E	9.8	10.2
b	0.5	0.7	E1	8.5	8.7
b1	0.6	0.8	L	14.9	15.4
c	1.25	1.35	L1	4.8	5.2
c1	0.45	0.55	L2	2.3	2.7
D	9.05	9.45	e	1.27BSC	
D1	6.65	7.05	θ	5°	10°
D2	0.65	1.05	θ_1	3°	8°

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.